

# PMZB290UN

### 20 V, single N-channel Trench MOSFET **20 January 2016**

**Product data sheet** 

#### 1. **General description**

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. **Features and benefits**

- Fast switching
- Trench MOSFET technology
- Low threshold voltage
- Ultra thin package profile with 0.37 mm height
- ElectroStatic Discharge (ESD) protection: 2 kV HBM

### **Applications**

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

#### Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	20	V
V <sub>GS</sub>	gate-source voltage			-8	-	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-	1	Α
Static characteristics						,	
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 4.5 V; $I_D$ = 200 mA; $T_j$ = 25 °C		-	290	350	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



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### 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	1 🔲	D I
2	S	source		
3	D	drain	Transparent top view  DFN1006B-3 (SOT883B)	G S 017aaa255

### 6. Ordering information

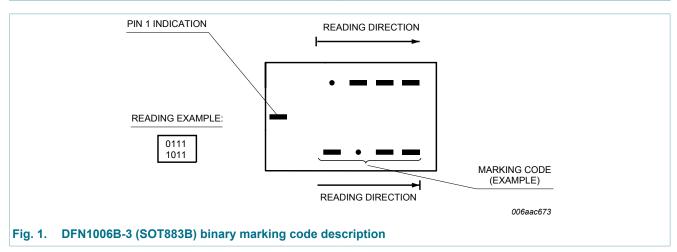
Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMZB290UN	DFN1006B-3	DFN1006B-3: leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B		

### 7. Marking

Table 4. Marking codes

Type number	Marking code
PMZB290UN	0000 0101



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### 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	20	V
$V_{GS}$	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	1	Α
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	0.6	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	4	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	360	mW
			[1]	-	715	mW
		T <sub>sp</sub> = 25 °C		-	2700	mW
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drai	in diode		•			
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	0.67	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

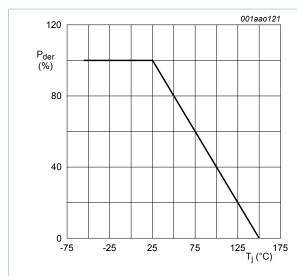


Fig. 2. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

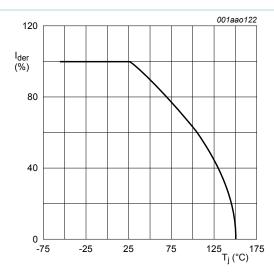


Fig. 3. Normalized continuous drain current as a function of junction temperature

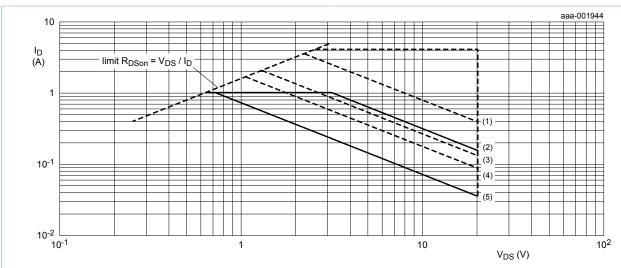
$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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I<sub>DM</sub> is single pulse

- (1)  $t_p = 1 \text{ ms}$
- (2) DC;  $T_{sp}$  = 25 °C
- (3)  $t_p = 10 \text{ ms}$
- (4)  $t_p = 100 \text{ ms}$
- (5) DC;  $T_{amb} = 25 \, ^{\circ}C$ ; drain mounting pad 1 cm<sup>2</sup>

Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
from ju	thermal resistance		[1]	-	305	360	K/W
	from junction to ambient		[2]	-	150	175	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	40	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

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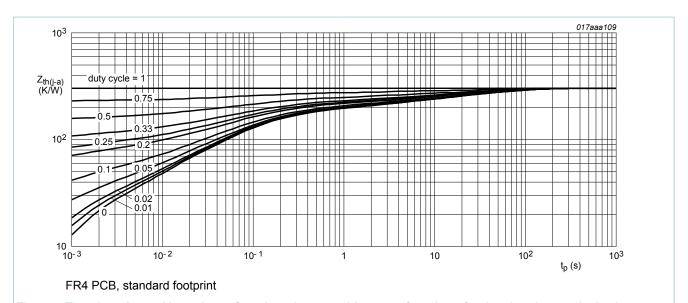
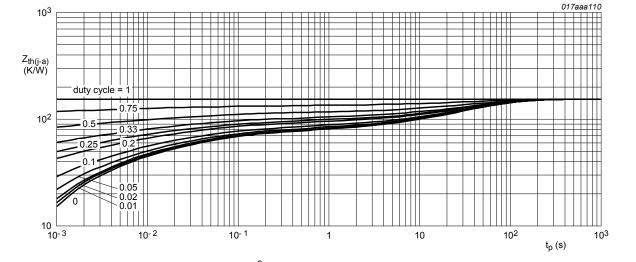


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm<sup>2</sup>

Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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### 10. Characteristics

Table 7. Characteristics

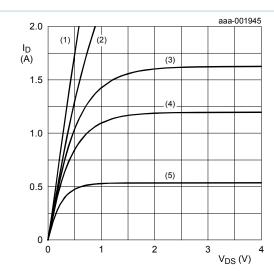
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 10 \mu A; V_{GS} = 0 V; T_j = 25 °C$	20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.45	0.7	0.95	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
		V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	100	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	5	μA
		$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	-5	μA
		V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μΑ
		$V_{GS}$ = -4.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-1	μΑ
		V <sub>GS</sub> = 2.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
		V <sub>GS</sub> = -2.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = 4.5 V; $I_D$ = 200 mA; $T_j$ = 25 °C	-	290	350	mΩ
	resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 200 mA; T <sub>j</sub> = 150 °C	-	460	560	mΩ
		V <sub>GS</sub> = 2.5 V; I <sub>D</sub> = 100 mA; T <sub>j</sub> = 25 °C	-	360	450	mΩ
		V <sub>GS</sub> = 1.8 V; I <sub>D</sub> = 75 mA; T <sub>j</sub> = 25 °C	-	460	650	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS} = 5 \text{ V}; I_D = 200 \text{ mA}; T_j = 25 \text{ °C}$	-	5.8	-	S
Dynamic ch	naracteristics		'	'		_
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 1 A; V <sub>GS</sub> = 4.5 V;	-	0.89	1.2	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C	-	0.13	-	nC
$Q_{GD}$	gate-drain charge		-	0.18	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 20 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	45	68	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	11	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	7	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 10 V; $R_L$ = 10 $\Omega$ ; $V_{GS}$ = 4.5 V;	-	4.5	9	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega$ ; $T_j = 25 ^{\circ}C$	-	10	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	18.5	37	ns
t <sub>f</sub>	fall time		-	5	-	ns
Source-dra	in diode		'	-		
$V_{SD}$	source-drain voltage	$I_S$ = 300 mA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.75	1.2	V
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 $T_i = 25 \,^{\circ}C$ 

(1)  $V_{GS} = 4.5 \text{ V}$ 

 $(2) V_{GS} = 2.5 V$ 

 $(3) V_{GS} = 2.0 V$ 

 $(4) V_{GS} = 1.8 V$ 

 $(5) V_{GS} = 1.5 V$ 

Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values

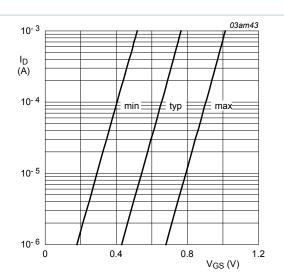
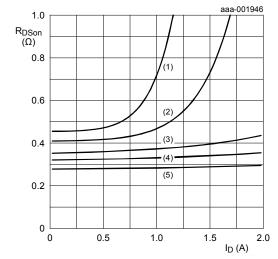


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25^{\circ}C; V_{DS} = 5V$$



 $T_i = 25 \,^{\circ}C$ 

(1)  $V_{GS} = 1.8 \text{ V}$ 

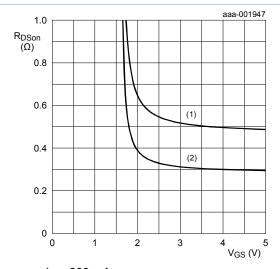
(2)  $V_{GS} = 2 V$ 

 $(3) V_{GS} = 2.5 V$ 

(4)  $V_{GS} = 3 V$ 

 $(5) V_{GS} = 4.5 V$ 





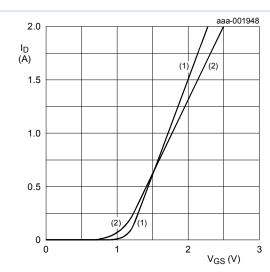
 $I_D = 800 \text{ mA}$ 

(1)  $T_i = 150 \, ^{\circ}C$ 

(2)  $T_i = 25 \, ^{\circ}C$ 

Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

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 $V_{DS} > I_D \times R_{DSon}$ (1)  $T_j = 25 \text{ °C}$ 

(2)  $T_j = 150 \, ^{\circ}C$ 

Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

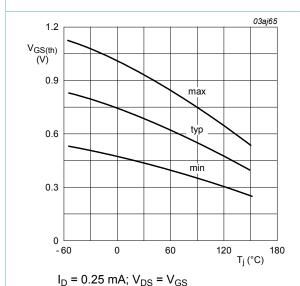


Fig. 13. Gate-source threshold voltage as a function of junction temperature

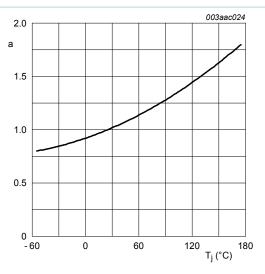


Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

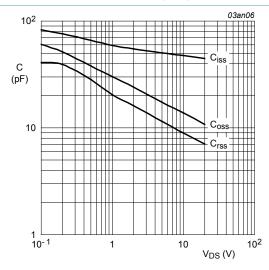


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1MHz$$

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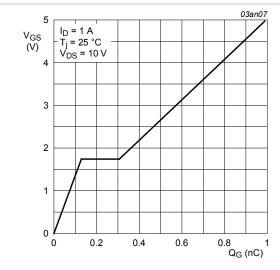


Fig. 15. Gate-source voltage as a function of gate charge; typical values

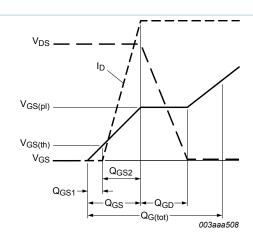
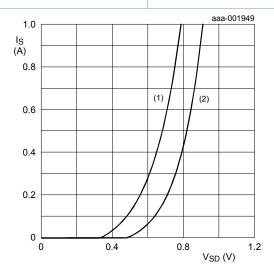


Fig. 16. Gate charge waveform definitions



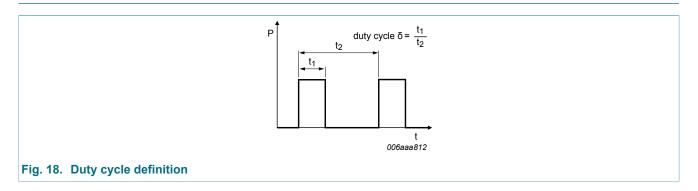
 $V_{GS} = 0 V$ (1)  $T_j = 150 \,^{\circ}C$ (2)  $T_i = 25 \,^{\circ}C$ 

Fig. 17. Source current as a function of source-drain voltage; typical values

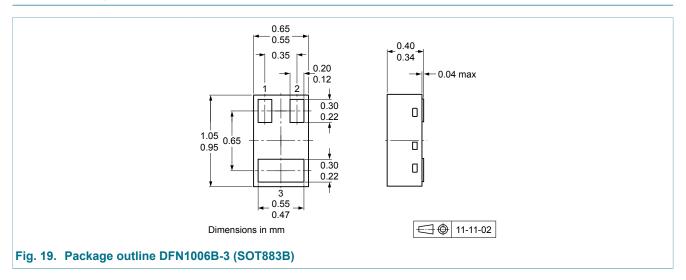
**Product data sheet** 

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### 11. Test information

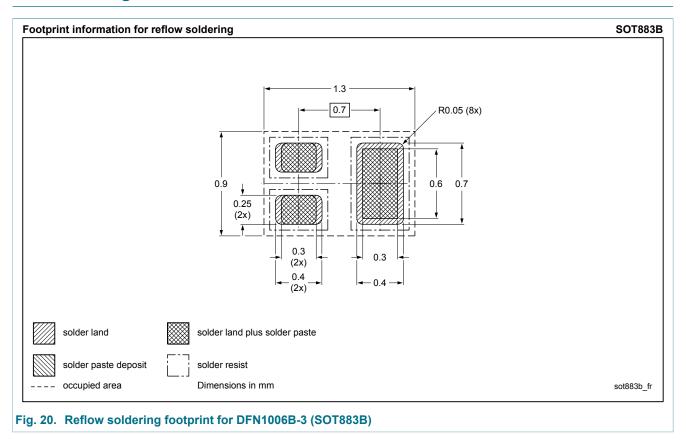


## 12. Package outline



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### 13. Soldering



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## 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PMZB290UN v.2	20160120	Product data sheet	-	PMZB290UN v.1		
Modifications:	values for gate leakage current and forward transconductance changed					
PMZB290UN v.1	20120511	Product data sheet	-	-		

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### 15. Legal information

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Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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